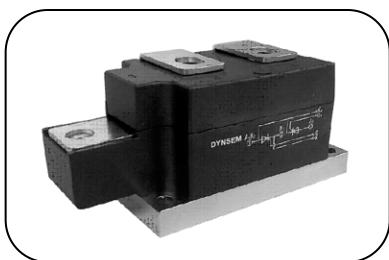




DSKT 200 Thyristor Modules



Features:

- Isolated mounting base 4000V~
- Pressure contact technology with Increased power cycling capability
- Space and weight saving

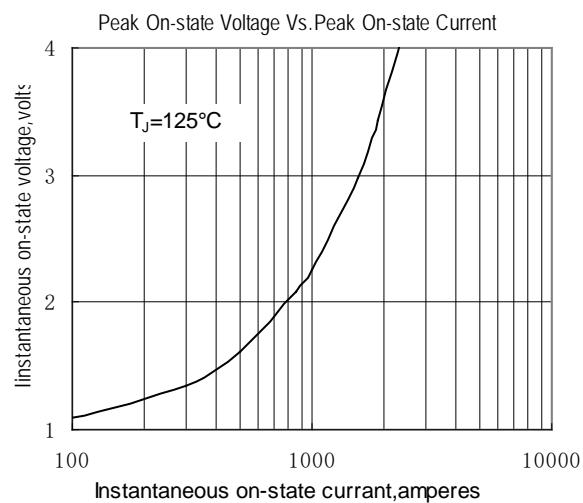
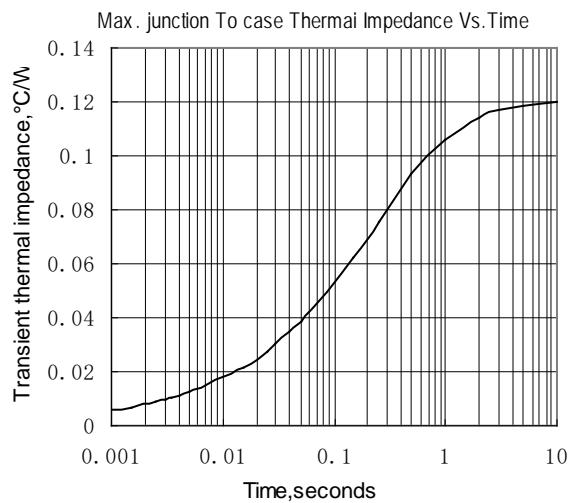
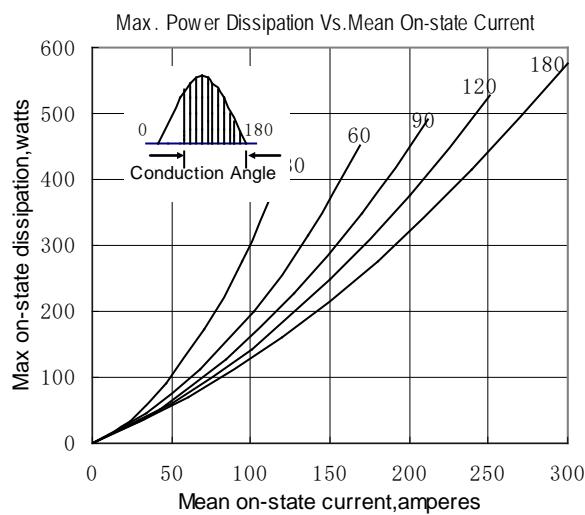
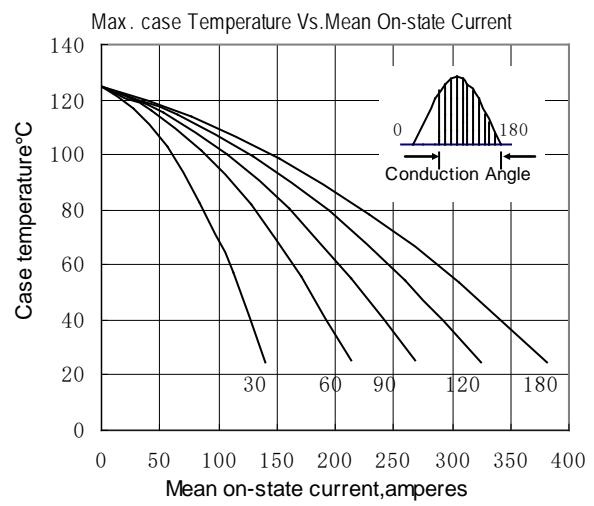
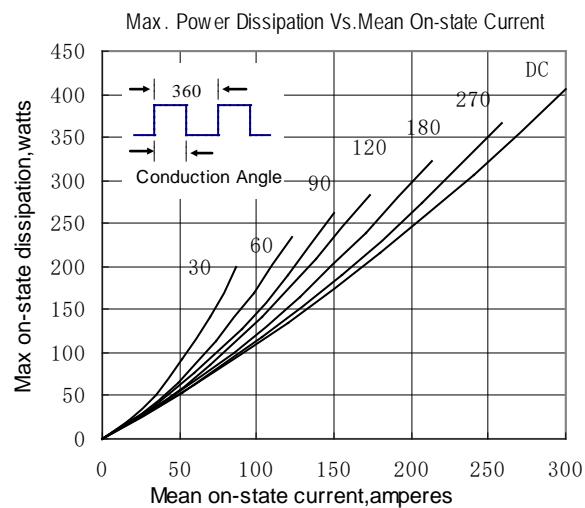
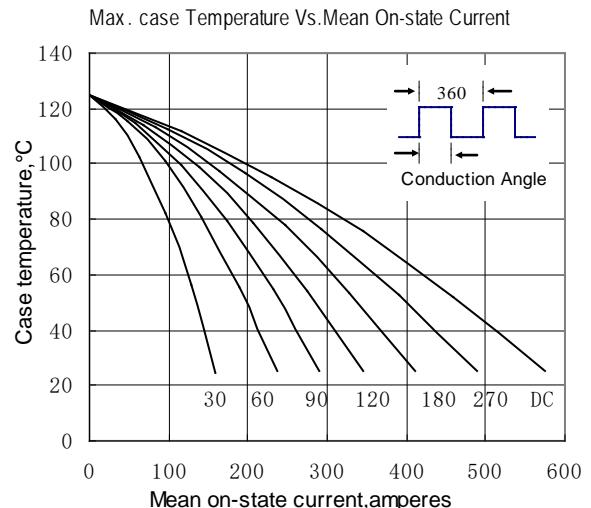
Typical Applications

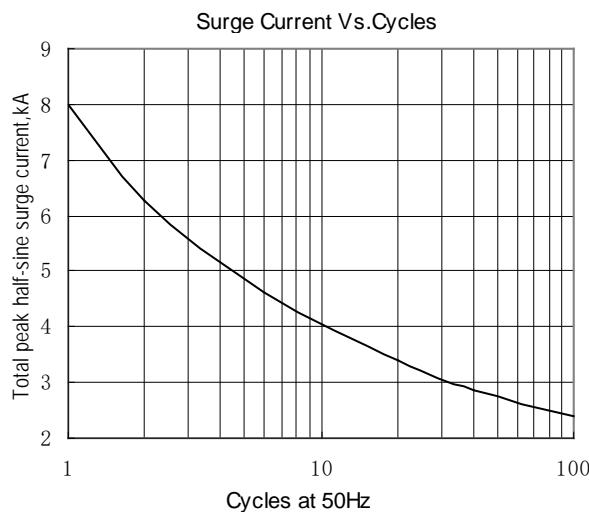
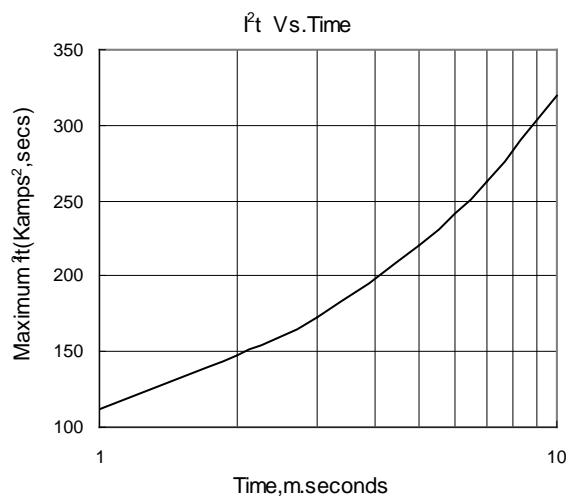
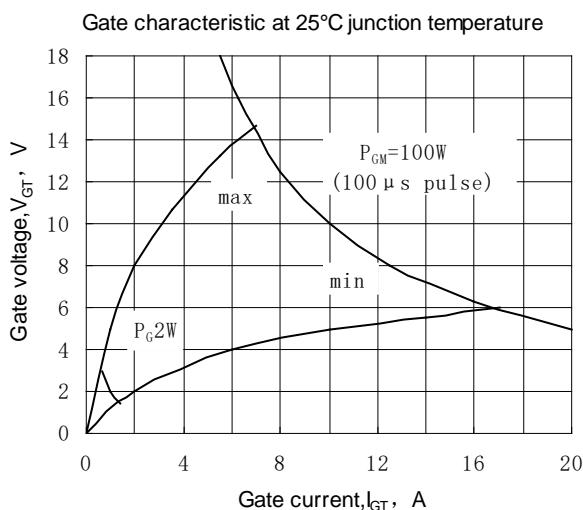
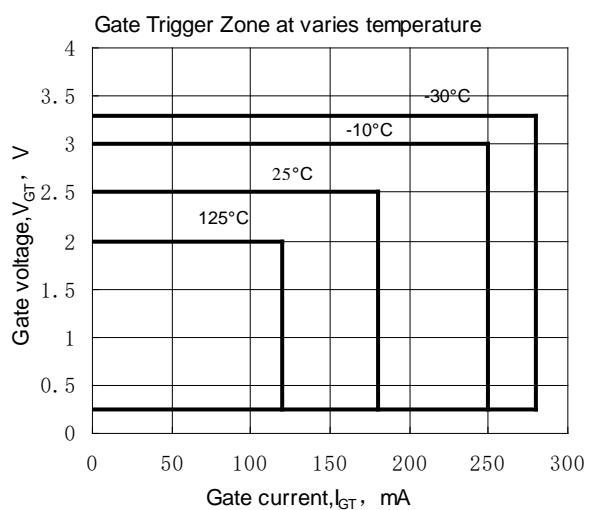
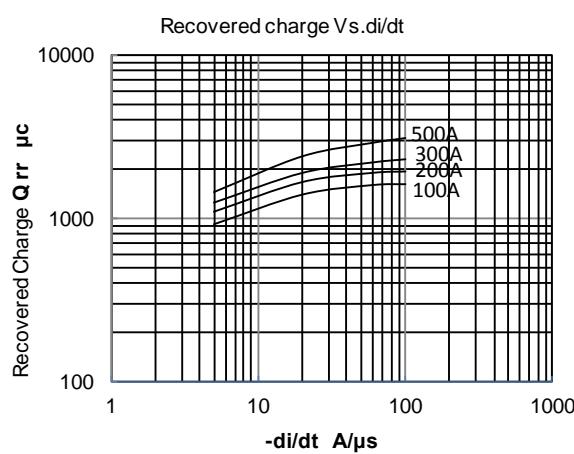
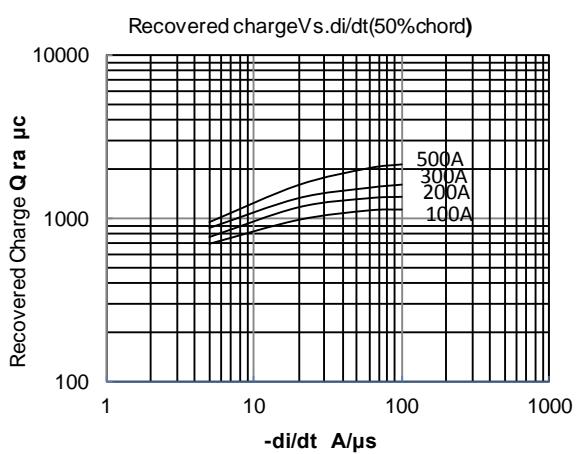
- AC/DC Motor drives
- Various rectifiers
- DC supply for PWM inverter

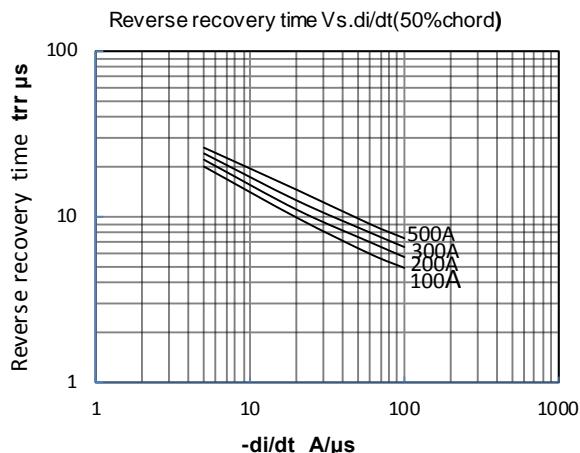
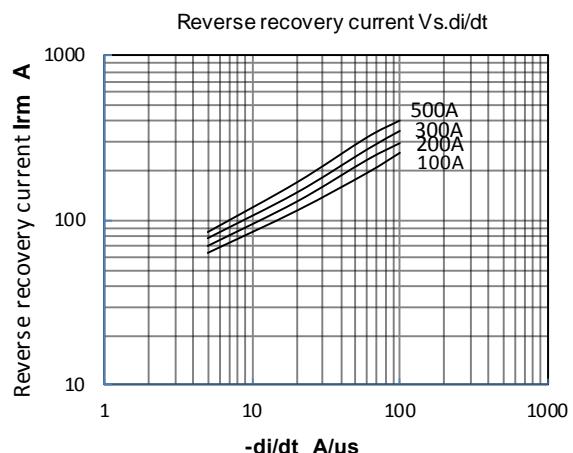
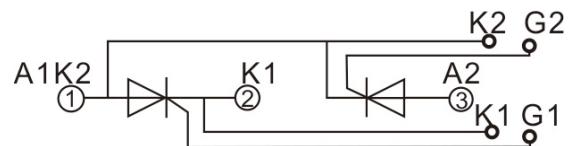
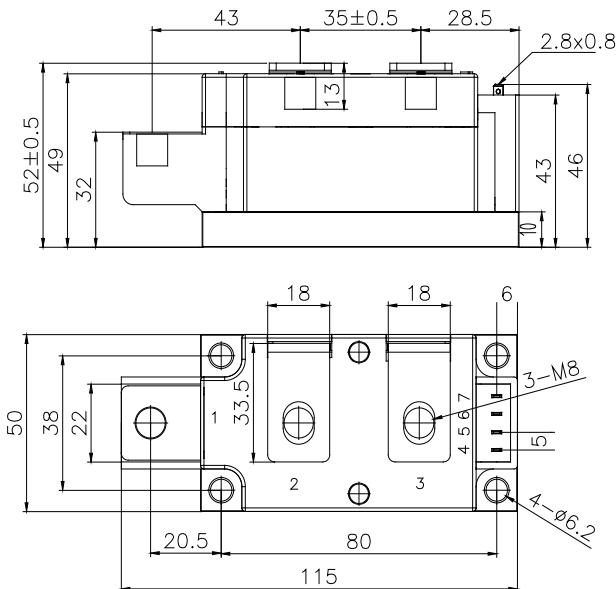
V_{DSM}, V_{RSM}	V_{DRM}, V_{RRM}	Type & Outline
2700V	2600V	DSKT 200-26
2900V	2800V	DSKT 200-28
3100V	3000V	DSKT 200-30
3300V	3200V	DSKT 200-32
3500V	3400V	DSKT 200-34
3700V	3600V	DSKT 200-36

DSPACK 3

SYMBOL	CHARACTERISTIC	TEST CONDITIONS	$T_J(^{\circ}\text{C})$	VALUE			UNIT
				Min	Type	Max	
$I_{T(AV)}$	Mean on-state current	180° half sine wave 50Hz Single side cooled, $T_c=85^{\circ}\text{C}$	125			200	A
$I_{T(RMS)}$	RMS on-state current		125			314	A
I_{DRM} I_{RRM}	Repetitive peak current	at V_{DRM} at V_{RRM}	125			35	mA
I_{TSM}	Surge on-state current	10ms half sine wave	125			8.0	KA
I^2t	I^2T for fusing coordination	$V_R=60\%V_{RRM}$				320	$\text{A}^2\text{s} \times 10^3$
V_{TO}	Threshold voltage		125			0.96	V
r_T	On-state slope resistance					1.30	$\text{m}\Omega$
V_{TM}	Peak on-state voltage	$I_{TM}=600\text{A}$	25			2.55	V
dv/dt	Critical rate of rise of off-state voltage	$V_{DM}=67\%V_{DRM}$	125			800	$\text{V}/\mu\text{s}$
di/dt	Critical rate of rise of on-state current	$I_{TM}=400\text{A}$, Gate source 1.5A $t_r \leq 0.5\mu\text{s}$ Repetitive	125			100	$\text{A}/\mu\text{s}$
I_{GT}	Gate trigger current		25	30		180	mA
V_{GT}	Gate trigger voltage	$V_A=12\text{V}$, $I_A=1\text{A}$		1.0		2.5	V
I_H	Holding current			20		150	mA
V_{GD}	Non-trigger gate voltage	$V_{DM}=67\%V_{DRM}$	125	0.2			V
$R_{th(j-c)}$	Thermal resistance Junction to case	Single side cooled per chip				0.120	$^{\circ}\text{C}/\text{W}$
$R_{th(c-h)}$	Thermal resistance case to heat sink	Single side cooled per chip				0.04	$^{\circ}\text{C}/\text{W}$
V_{iso}	Isolation voltage	50Hz, R.M.S, $t=1\text{min}$, $I_{iso}=1\text{mA}(\text{MAX})$		4000			V
F_m	Thermal connection torque (M8)				12.0		$\text{N}\cdot\text{m}$
	Mounting torque (M6)				6.0		$\text{N}\cdot\text{m}$
T_{stg}	Stored temperature			-40		125	$^{\circ}\text{C}$
W_t	Weight				820		g
Outline	DSPACK 3						


Fig.1

Fig.2

Fig.3

Fig.4

Fig.5

Fig.6


Fig.7

Fig.8

Fig.9

Fig.10

Fig.11

Fig.12


Fig.13

Fig.14
Outline:

DSKT
DSPACK 3